### August 2001



# FDP2570/FDB2570

# 150V N-Channel PowerTrench<sup>®</sup> MOSFET

### **General Description**

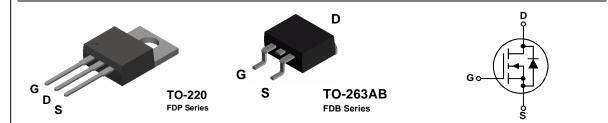
This N-Channel MOSFET has been designed specifically for switching on the primary side in the isolated DC/DC converter application. Any application requiring a 150V MOSFETs with low on-resistance and fast switching will benefit.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $RDS_{(ON)}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

### Features

- 22 A, 150 V.  $R_{DS(ON)} = 80 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$  $R_{DS(ON)} = 90 \text{ m}\Omega @ V_{GS} = 6 \text{ V}$
- Low gate charge (40nC typical)
- · Fast switching speed
- High performance trench technology for extremely low R<sub>DS(ON)</sub>
- 175°C maximum junction temperature rating



### Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage		150	V	
V <sub>GSS</sub>	Gate-Source Voltage		± 20	V	
I <sub>D</sub>	Drain Current – Continuous	(Note 1)	22	А	
	- Pulsed	(Note 1)	50	А	
PD	Total Power Dissipation @ T <sub>c</sub> = 25°C		93	W	
	Derate above 25°C		0.63	W°/C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperatur	re Range	-65 to +175	°C	

# Thermal Characteristics

$R_{ ext{ ext{ ext{ ext{ ext{ ext{ ext{ ext$	Thermal Resistance, Junction-to-Case	1.6	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

### Package Marking and Ordering Information

FDB2570 FDB2570 13" 24mm	000
	800 units
FDP2570 FDP2570 Tube n/a	45 units

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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-Sc	burce Avalanche Ratings (Note ·	1)			1	l
W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 75 \text{ V}, \qquad I_D = 11 \text{ A}$			375	mJ
I <sub>AR</sub>	Maximum Drain-Source Avalanche Current				11	A
Off Char	acteristics					
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$		154		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 120 \text{ V},  V_{\text{GS}} = 0 \text{ V}$			1	μA
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V},  V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2	2.6	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_{J}}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$		-7		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source	$V_{GS} = 10 \text{ V}, \qquad I_D = 11 \text{ A}$		61	80	mΩ
	On–Resistance	$V_{GS} = 6.0 \text{ V}, \qquad I_D = 10 \text{ A} \\ V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}, T_J = 125^{\circ}\text{C}$		63 127	90 175	
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 10 \text{ V}$	25			А
<b>g</b> fs	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 11 \text{ A}$		39		S
Dvnamic	Characteristics			•	•	•
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 75 V$ , $V_{GS} = 0 V$ ,		1911		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		106		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			33		pF
Switchin	g Characteristics (Note 2)			•	•	•
t <sub>d(on)</sub>	Turn–On Delay Time	$V_{DD} = 75 V$ , $I_D = 1 A$ ,		12	22	ns
tr	Turn–On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		5	10	ns
t <sub>d(off)</sub>	Turn–Off Delay Time	1		33	53	ns
t <sub>f</sub>	Turn–Off Fall Time	1		23	37	ns
Qg	Total Gate Charge	$V_{DS} = 75 V$ , $I_{D} = 11 A$ ,		40	56	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		7		nC
Q <sub>gd</sub>	Gate–Drain Charge	7		12		nC

Is	Maximum Continuous Drain-Source Diode Forward Current				22	А
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \ V,  I_S = 11 \ A$	(Note 2)	0.83	1.3	V

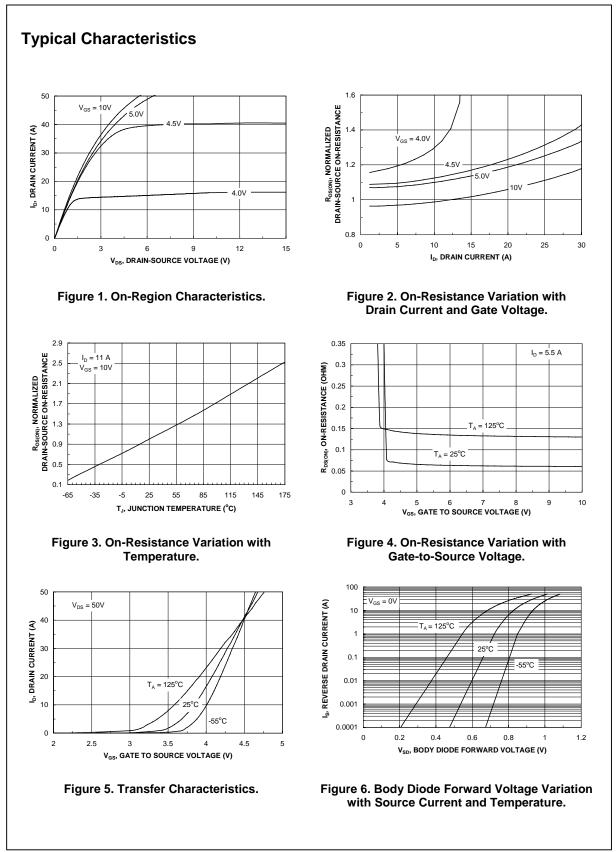
Notes:

1. Calculated continuous current based on maximum allowable junction temperature.

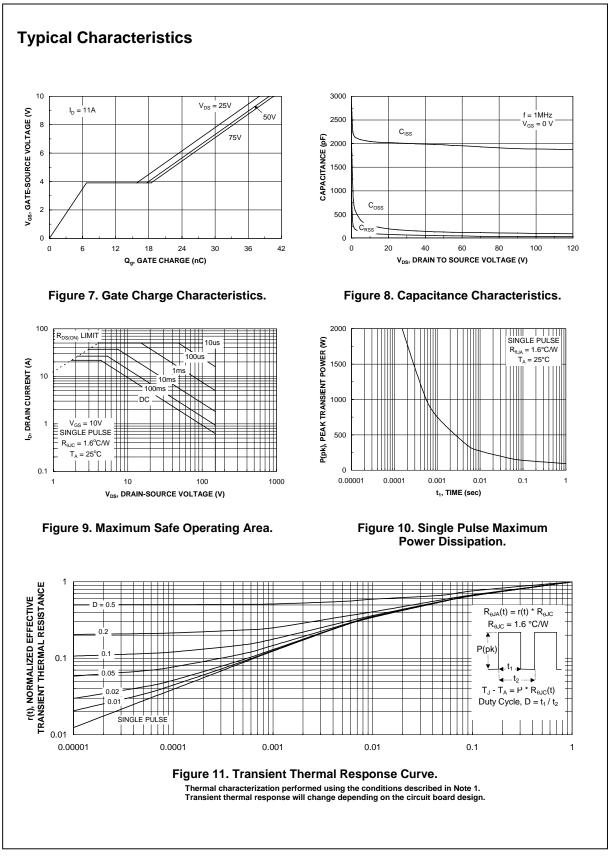
2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty Cycle < 2.0%

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FDP2570/FDB2570 Rev C(W)

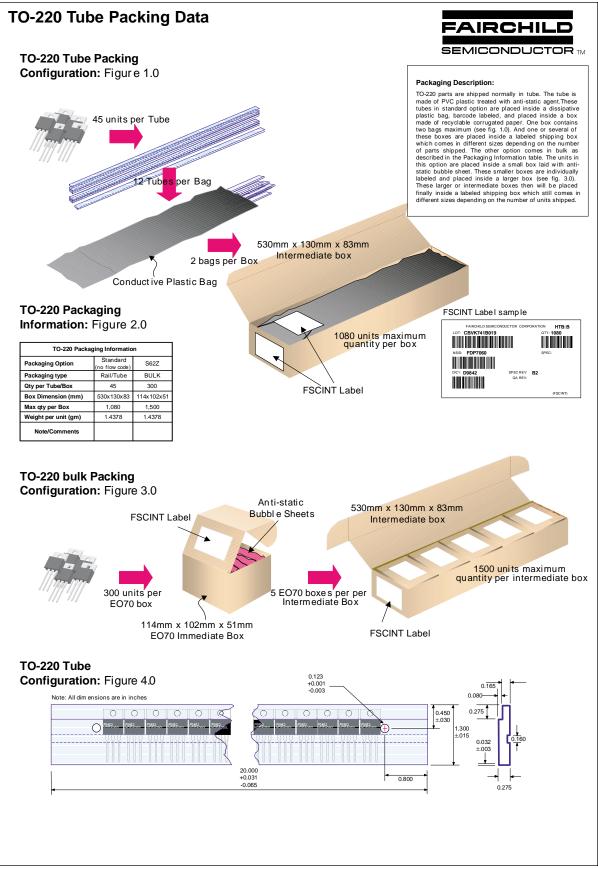


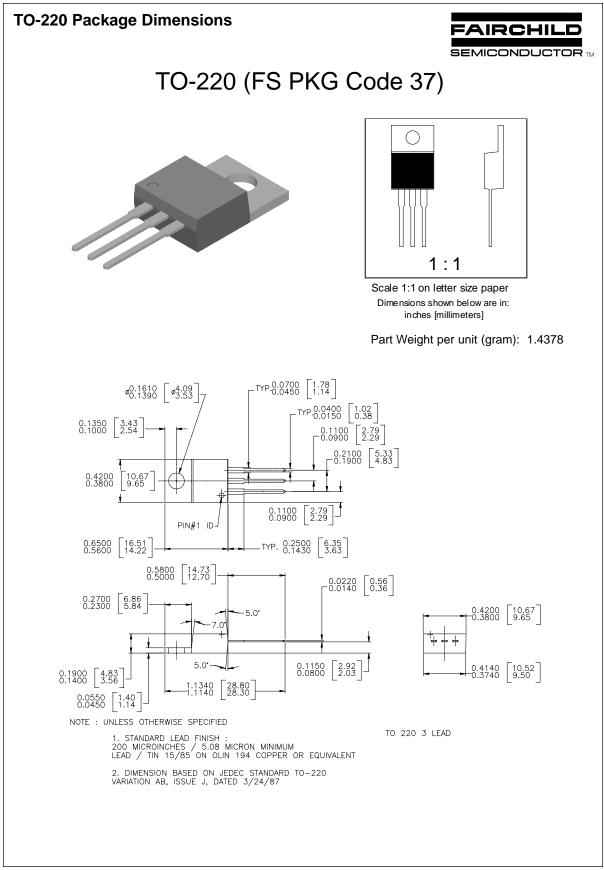
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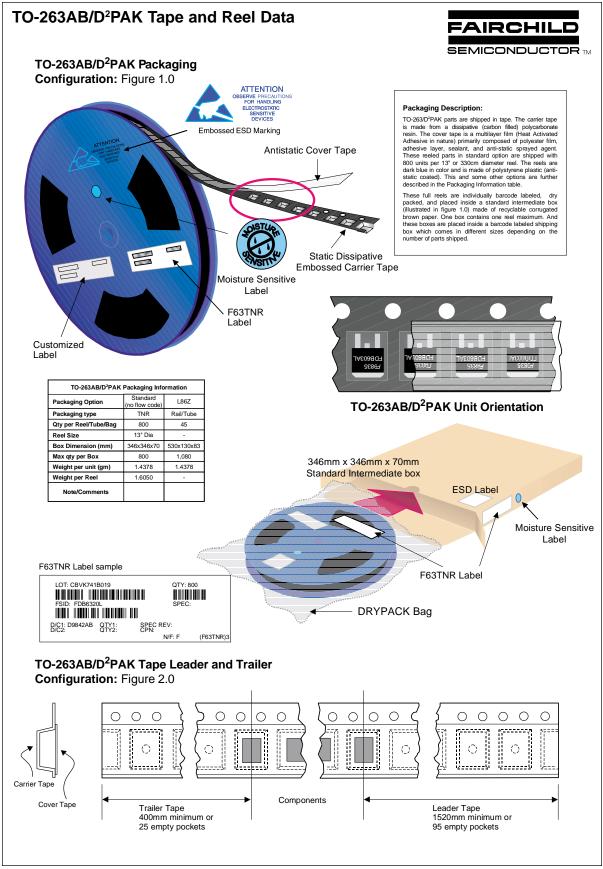


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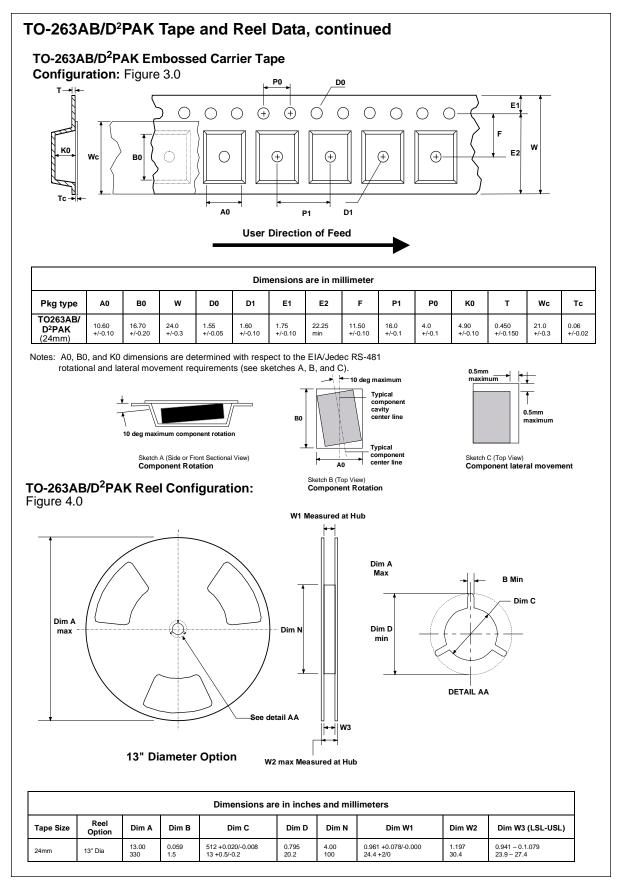
FDP2570/FDB2570 Rev C(W)

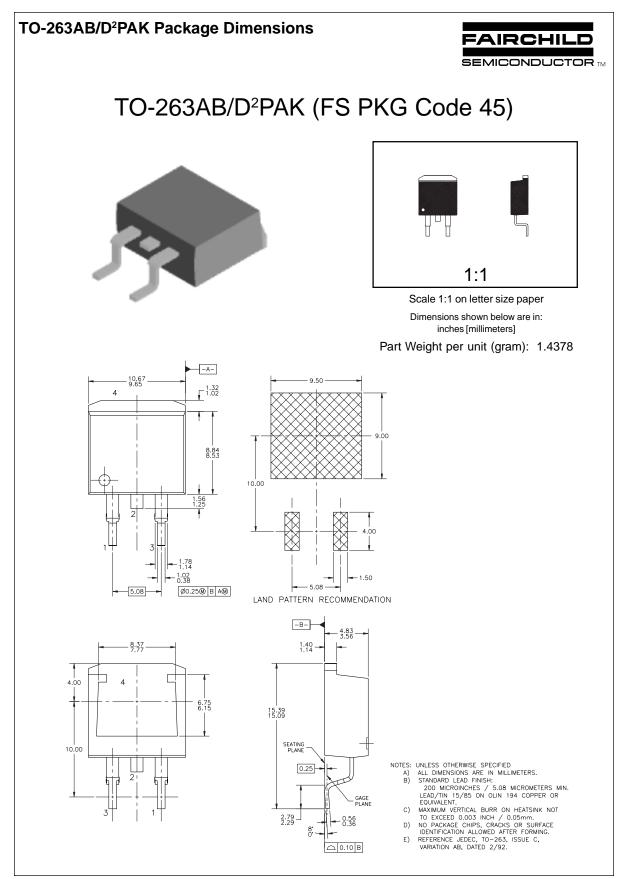






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